OPS666, OPS667, OPS691, OPS692, OPS693, OPS698

Electronics

Features:

- High current transfer ratio
- Low-cost plastic package
- Lateral side-looking clear plastic package (OPS691, OPS692, OPS693 and OPS698)



Description:

Each LED/Photosensor pair in the series consists of a gallium arsenide infrared emitting diode and a NPN silicon phototransistor, mounted in a T-1 package (OPS666, OPS667) or in a matched lateral side-looking plastic package (OPS691, OPS692, OPS693 and OPS698).

Matched pairs are desirable where the application is unique and the quantity required does not justify assembly tooling costs. If separation between the LED and sensor is greater than two times the specified $IC_{(ON)}$ distance, proper alignment becomes critical. Although sold as pairs, emitters and sensors are packaged separately for handling ease.

Please note that the sensor is sensitive to ambient light.

Applications:

- Non-contact reflective object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor

			Ordering Information	
Part Number	Output	Package Style	Description	Lead Length
OPS666	Transistor	T-1	Gallium arsenide infrared emitting diode (OP165) NPN silicon phototransistor (OP505)	0.50" (`1.700 mm)
OPS667	Transistor	T-1	Gallium arsenide infrared emitting diode (OP165) NPN silicon phototransistor (OP505)	0.50" (`1.700 mm)
OPS691	Transistor	Lateral Side-looking	Gallium arsenide infrared emitting diode (OP140) NPN silicon phototransistor (OP550)	0.50" (`1.700 mm)
OPS692	Transistor	Lateral Side-looking	Gallium arsenide infrared emitting diode (OP140) NPN silicon phototransistor (OP550)	0.50" (`1.700 mm)
OPS693	Transistor	Lateral Side-looking	Gallium arsenide infrared emitting diode (OP140) NPN silicon phototransistor (OP550)	0.50" (`1.700 mm)
OPS698	Transistor	Lateral Side-looking	Gallium arsenide infrared emitting diode (OP145) NPN silicon phototransistor (OP555)	0.50" (`1.700 mm)

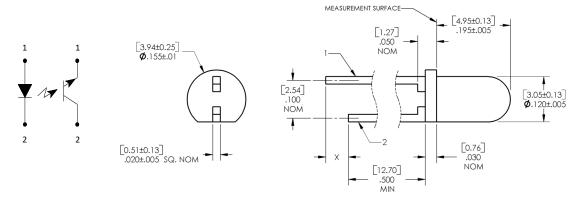


OPS666, OPS667, OPS691, OPS692, OPS693, OPS698



Electrical Specifications

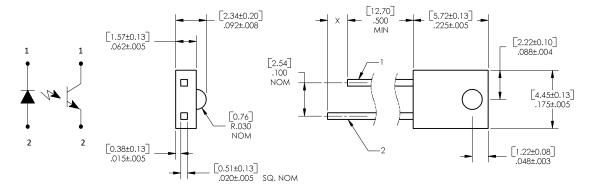
OPS666, OPS667



DIMENSIONS ARE IN INCHES AND [MILLIMETERS].

Pin #	LED & Diode X=0.060" (1.5	Transistor X=0" (0.0 mm)
1	Anode	Emitter
2	Cathode	Collector

OPS691, OPS692, OPS693



DIMENSIONS ARE IN INCHES AND [MILLIMETERS].

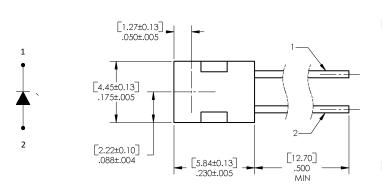
Pin#	LED X=0.060" (1.5	Sensor X=0" (0.0 mm)
1	Cathode	Emitter/Anode
2	Anode	Collector/Cathode

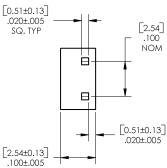
OPS666, OPS667, OPS691, OPS692, OPS693, OPS698



Electrical Specifications

OPS698





DIMENSIONS ARE IN INCHES AND [MILLIMETERS].

Pin#	Diode		
1	Cathode		
2	Anode		



OPS666, OPS667, OPS691, OPS692, OPS693, OPS698

Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage & Operating Temperature Range	-40° C to +100° C
Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron]	260° C ⁽¹⁾
Input Diode	
Forward DC Current	50 mA
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A
Reverse DC Voltage	2.0 V
Power Dissipation	100 mW ⁽²⁾
Output Photosensor (OPS666/667) or Output Phototransistor (691/692/693/698)	
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Power Dissipation	100 mW ⁽²⁾



OPS666, OPS667, OPS691, OPS692, OPS693, OPS698

Electrical Specifications

Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Input Diod	e					
V_{F}	Forward Voltage	-	-	1.6	V	I _F = 20 mA
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V
Output Pho	ototransistor	•				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	I _C = 100 μA, E _E = 0
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5.0	-	-	V	I _E = 100 μA, E _E = 0
I _{CEO}	Collector-Emitter Dark Current OPS666/667 OPS691/692/693 OPS698	- - -		100 100 100	nA nA nA	$V_{CE} = 15 \text{ V}, I_F = 0, I_E = 0$ $V_{CE} = 10 \text{ V}, I_F = 0, I_E = 0$ $V_{CE} = 10 \text{ V}, I_F = 0, I_E = 0$
Combined		•		•		
V _{CE(SAT)}	Collector-Emitter Saturation Voltage OPS666/667 OPS691/692/693 OPB698		- - -	- 0.4 0.4	- V V	- I _F = 20 mA, I _C = 50 μA ⁽³⁾ I _F = 20 mA, I _C = 50 μA ⁽³⁾
I _{C(ON)}	On-State Collector Current OPS666 OPS667 OPS691 OPS692	1.0 5.0 500 1.0	-	-	mA mA μA mA	$V_{CE} = 5 \text{ V}, I_F = 20 \text{ mA}^{(3)}$ $V_{CE} = 10 \text{ V}, I_F = 20 \text{ mA}^{(3)}$
	OPS693, OPS698	2.0	-	-	mA	

Notes:

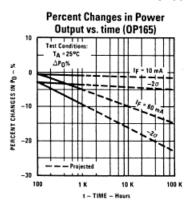
- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 1.33 mW/° C above 25° C.
- (3) Distance from lens tip to lens tip is 0.250" (6.35 mm) OPS666, OPS667
 Distance from lens tip to lens tip is 0.125" (3.175 mm) OPS691 thru OPS698

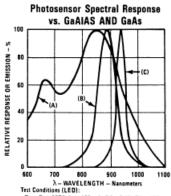




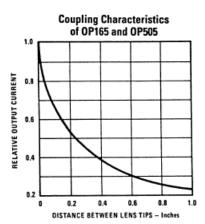
Performance

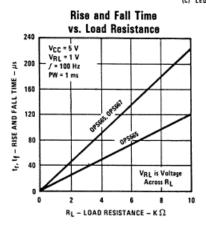
OPS666, OPS667

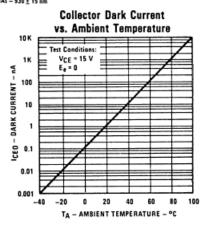


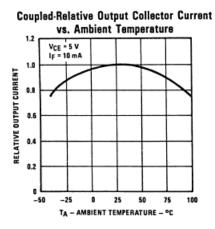


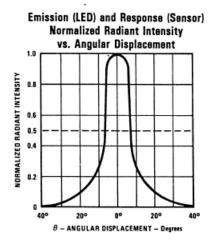
Test Conditions (LEO): TA = TJ = 25°C; IF = 100 mA, DC = 0.1%, PW = 100 µs Peak Wavelength - Ap: (A) XSTR = 850 ± 30 nm (B) LED GAAIA = 890 ± 20 nm (C) LEO GAA = 930 ± 15 nm

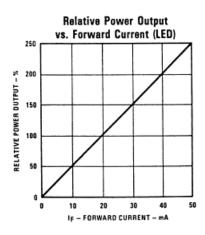










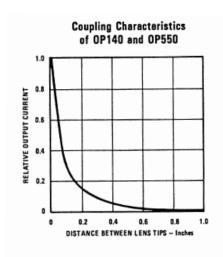


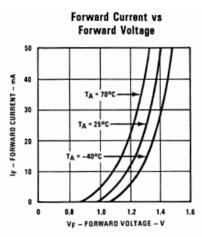


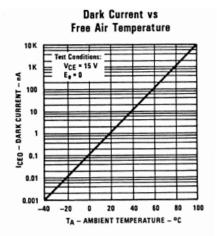


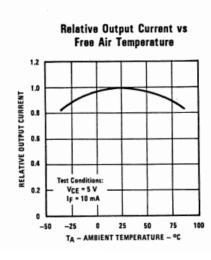
Performance

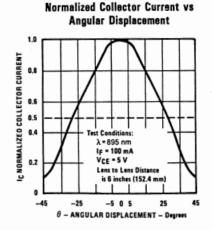
OPS691, OPS692, OPS693

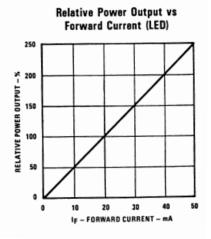












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